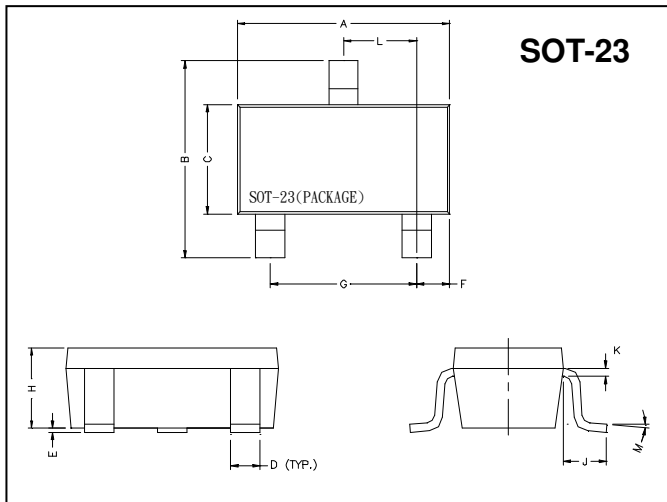
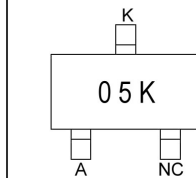


**G402SD****SURFACE MOUNT, SCHOTTKY BARRIER DIODE  
VOLTAGE 30V, CURRENT 0.3A****Description**

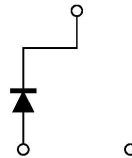
The G402SD is high frequency rectification for switching power supply.

**Package Dimensions**

Marking :



Circuit :



| REF. | Millimeter |      | REF. | Millimeter |      |
|------|------------|------|------|------------|------|
|      | Min.       | Max. |      | Min.       | Max. |
| A    | 2.70       | 3.10 | G    | 1.90       | REF. |
| B    | 2.40       | 2.80 | H    | 1.00       | 1.30 |
| C    | 1.40       | 1.60 | K    | 0.10       | 0.20 |
| D    | 0.35       | 0.50 | J    | 0.40       | -    |
| E    | 0          | 0.10 | L    | 0.85       | 1.15 |
| F    | 0.45       | 0.55 | M    | 0°         | 10°  |

**Absolute Maximum Ratings at TA = 25°C**

| Parameter                                                   | Symbol           | Ratings    | Unit |
|-------------------------------------------------------------|------------------|------------|------|
| Junction Temperature                                        | T <sub>j</sub>   | +125       | °C   |
| Storage Temperature                                         | T <sub>stg</sub> | -55 ~ +125 | °C   |
| Maximum Recurrent Peak Reverse Voltage                      | V <sub>RRM</sub> | 30         | V    |
| Maximum RMS Voltage                                         | V <sub>RMS</sub> | 21         | V    |
| Maximum DC Blocking Voltage                                 | V <sub>DC</sub>  | 30         | V    |
| Peak Forward Surge Current at 8.3mSec single half sine-wave | I <sub>FSM</sub> | 3.0        | A    |
| Typical Junction Capacitance between Terminal (Note 1)      | C <sub>J</sub>   | 40         | pF   |
| Maximum Average Forward Rectified Current                   | I <sub>o</sub>   | 0.3        | A    |
| Total Power Dissipation                                     | PD               | 225        | mW   |

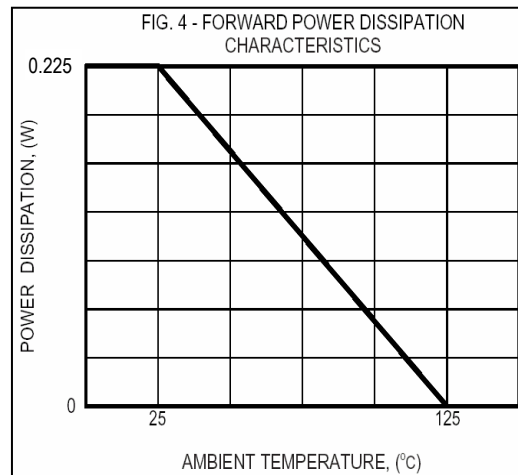
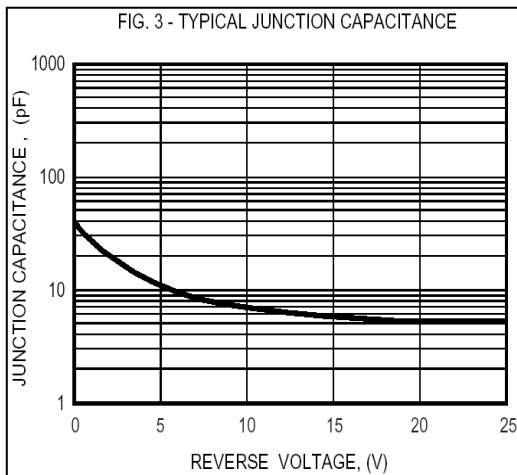
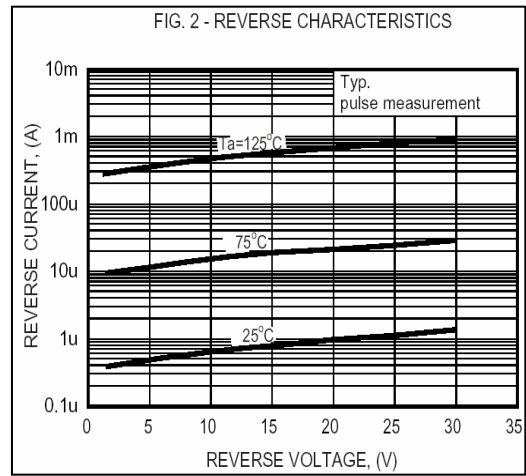
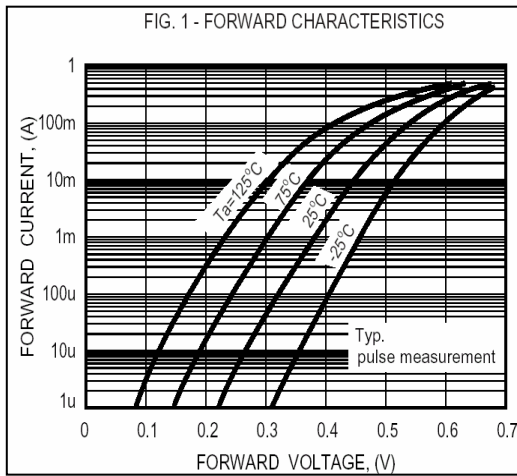
**Electrical Characteristics** (at TA = 25°C unless otherwise noted)

| Parameter                             | Symbol             | Min. | Typ. | Max. | Unit | Test Conditions       |
|---------------------------------------|--------------------|------|------|------|------|-----------------------|
| Reverse Breakdown Voltage             | V <sub>(BR)R</sub> | 30   | -    | -    | V    | I <sub>R</sub> =100μA |
| Maximum Instantaneous Forward Voltage | V <sub>F</sub>     | -    | -    | 500  | mV   | I <sub>F</sub> =300mA |
| Maximum Average Reverse Current       | I <sub>R</sub>     | -    | -    | 50   | μA   | VR1=10V               |
|                                       |                    | -    | -    | 100  | μA   | VR2=30V               |

Notes: 1. Measured at 1.0 MHz and 0 reverse bias voltage.

2. ESD sensitive product handling required.

## Characteristics Curve

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